

PHOTOCOUPLER DC004444

PS2811-1,PS2811-4

HIGH CTR 4, 16-PIN SOP PHOTOCOUPLER

-NEPOC[™] Series-

DESCRIPTION

The PS2811-1 and PS2811-4 are optically coupled isolators containing a GaAs light emitting diode and an NPN silicon phototransistor in a plastic SOP for high density applications.

The package is an SOP (Small Outline Package) type for high density mounting applications.

FEATURES

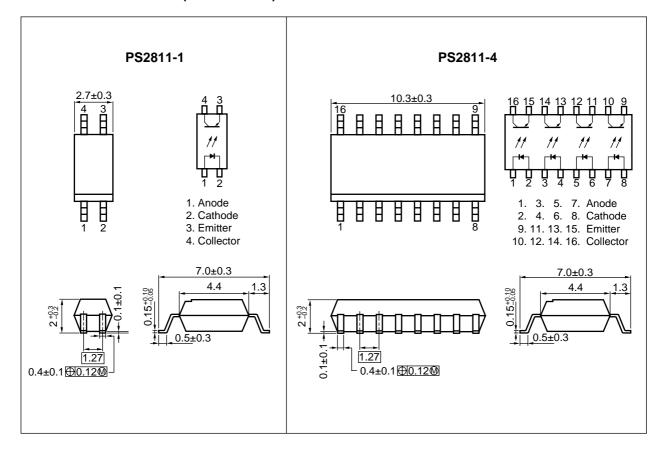
- High current transfer ratio (CTR = 200 % TYP. @ IF = 1mA)
- High isolation voltage (BV = 2 500 Vr.m.s.)
- Small and thin package (4, 16-pin SOP, Pin pitch 1.27 mm)
- Ordering number of taping product: PS2811-1-F3, F4, PS2811-4-F3, F4

APPLICATIONS

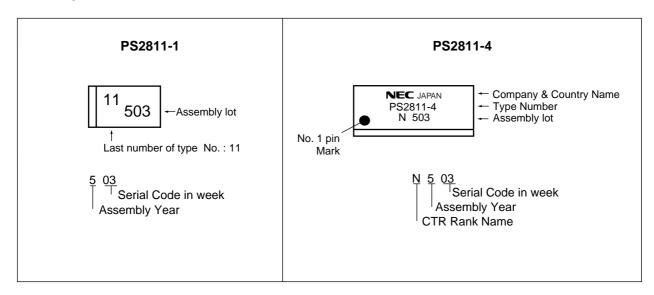
- · Programmable logic controllers
- · Small power supply
- Hybrid IC
- Modem/FAX

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PACKAGE DIMENSIONS (in millimeters)



MARKING





ORDERING INFORMATION

Part Number	Package	Packing Style	Safety Standards Approval	Application Part Number*1
PS2811-1	4-pin SOP	50 pcs (Tape 50 pcs cut)	UL, BSI approved	PS2811-1
PS2811-1-F3		Embossed Tape 3 500 pcs/reel		
PS2811-1-F4				
PS2811-4	16-pin SOP	Magazine Case 45 pcs		PS2811-4
PS2811-4-F3		Embossed Tape 2 500 pcs/reel		
PS2811-4-F4				

^{*1} For the application of the Safety Standard, following part number should be used.

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ABSOLUTE MAXIMUM RATINGS (TA = 25 °C, unless otherwise specified)

Parameter			Ratings		
		Symbol	PS2811-1	PS2811-4	Unit
Diode	Forward Current (DC)	I F	50		mA
	Reverse Voltage	VR	6		٧
	Power Dissipation Derating	∆P₀/°C	0.6	0.7	mW/°C
	Power Dissipation	Po	60	70	mW/ch
	Peak Forward Current*1	I FP	0.5		Α
Transistor	Collector to Emitter Voltage	Vceo	40		٧
	Emitter to Collector Voltage	VECO		5	V
	Collector Current	lc	4	10	mA/ch
	Power Dissipation Derating	∆Pc/°C	1.2		mW/°C
	Power Dissipation	Pc	120		mW/ch
Isolation Voltage*2		BV	2 500		Vr.m.s.
Operating Ambient Temperature		TA	−55 to +100		°C
Storage Temperature		T _{stg}	-55 to +150		°C

^{*1} PW = 100 μ s, Duty Cycle = 1 %

^{*2} AC voltage for 1 minute at T_A = 25 °C, RH = 60 % between input and output

ELECTRICAL CHARACTERISTICS (TA = 25 °C)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Diode	ode Forward Voltage		I _F = 5 mA		1.15	1.4	V
	Reverse Current	I R	VR = 5 V			5	μΑ
	Terminal Capacitance	Ct	V = 0 V, f = 1 MHz		30		pF
Transistor	Collector to Emitter Current	ICEO	IF = 0 mA, VCE = 40 V			100	nA
Coupled	Current Transfer Ratio	CTR	I _F = 1 mA, V _{CE} = 5 V	100	200	400	%
	Collector Saturation Voltage	VCE (sat)	IF = 1 mA, Ic = 0.2 mA			0.3	V
	Isolation Resistance	R _{I-O}	Vi-o = 1 kVdc	10 ¹¹			Ω
	Isolation Capacitance	C _{I-O}	V = 0 V, f = 1 MHz		0.4		pF
	Rise Time*2	tr	$Vcc = 5 \text{ V}, \text{ Ic} = 2 \text{ mA}, \text{ RL} = 100 \Omega$		4		μs
	Fall Time*2	t f			5		

*1 CTR rank

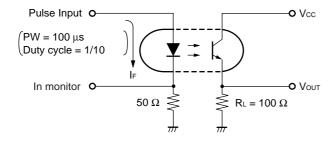
PS2811-1

N: 100 to 400 (%) K: 200 to 400 (%) L: 150 to 300 (%) M: 100 to 200 (%)

PS2811-4

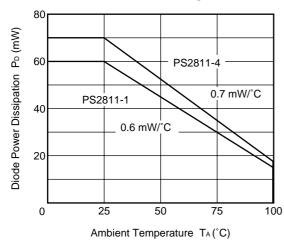
N: 100 to 400 (%)

*2 Test circuit for switching time

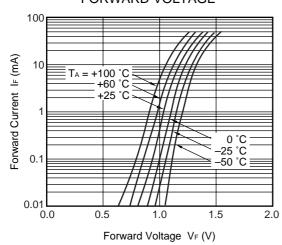


TYPICAL CHARACTERISTICS (TA = 25 °C, unless otherwise specified)

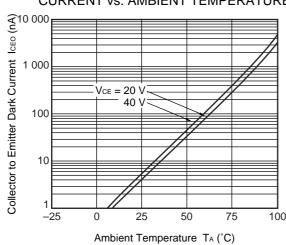




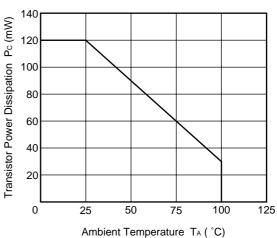
FORWARD CURRENT vs. FORWARD VOLTAGE



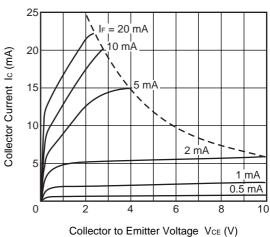
COLLECTOR TO EMITTER DARK CURRENT vs. AMBIENT TEMPERATURE



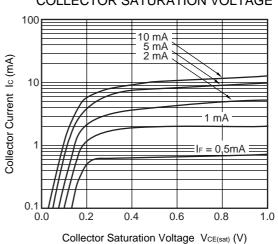
TRANSISTOR POWER DISSIPATION vs. AMBIENT TEMPERATURE



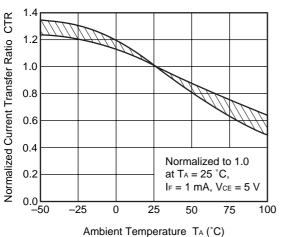
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



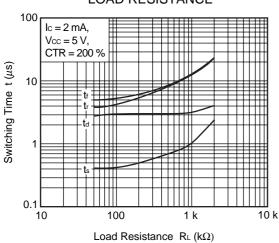
COLLECTOR CURRENT vs. COLLECTOR SATURATION VOLTAGE



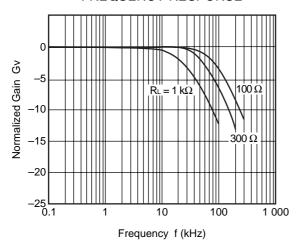
NORMALIZED CURRENT TRANSFER RATIO vs. AMBIENT TEMPERATURE



SWITCHING TIME vs. LOAD RESISTANCE

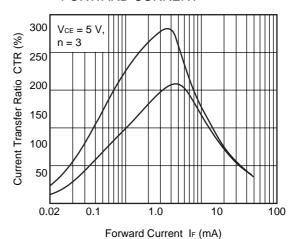


FREQUENCY RESPONSE

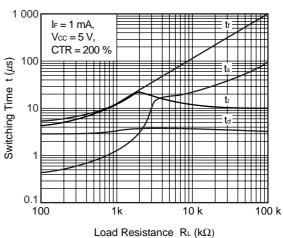


Remark The graphs indicate nominal characteristics.

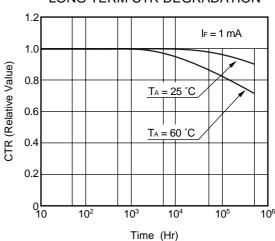
CURRENT TRANSFER RATIO vs. FORWARD CURRENT



SWITCHING TIME vs. LOAD RESISTANCE

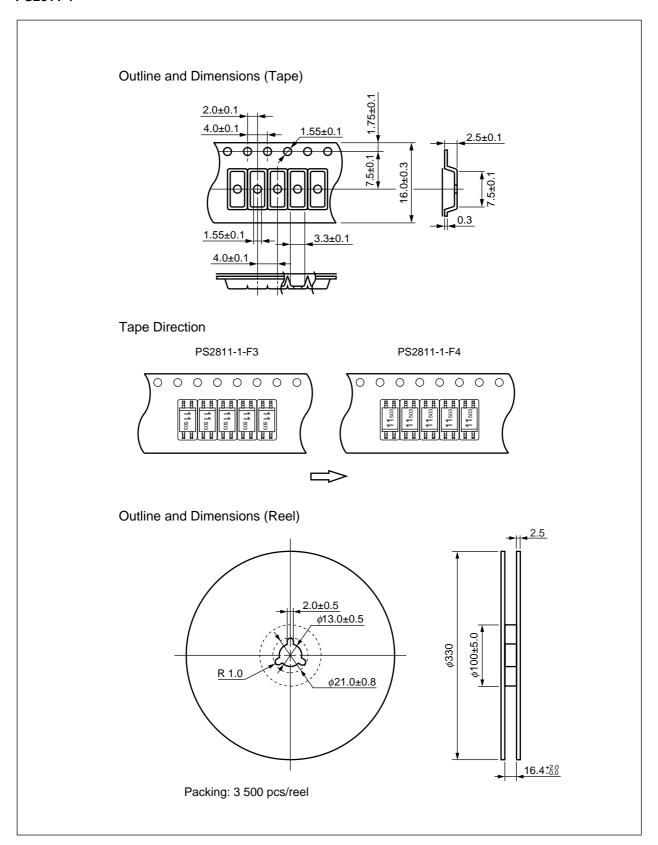


LONG TERM CTR DEGRADATION

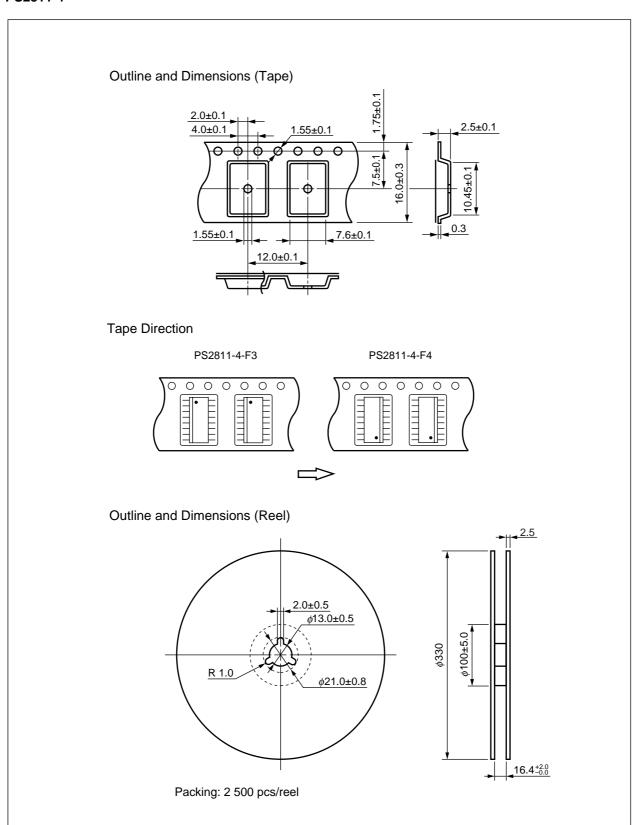


TAPING SPECIFICATIONS (in millimeters)

PS2811-1



PS2811-4



RECOMMENDED SOLDERING CONDITIONS

(1) Infrared reflow soldering

Peak reflow temperature
 235 °C or below (package surface temperature)

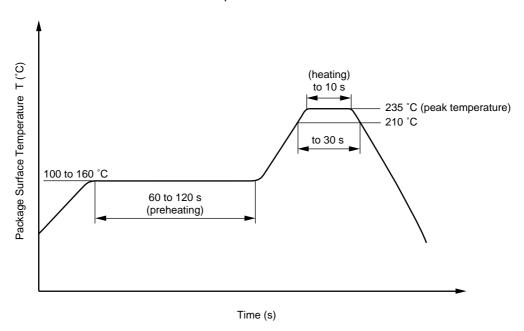
• Time of temperature higher than 210 °C 30 seconds or less

• Number of reflows Three

Flux
 Rosin flux containing small amount of chlorine (The flux with a

maximum chlorine content of 0.2 Wt % is recommended.)

Recommended Temperature Profile of Infrared Reflow



(2) Dip soldering

• Temperature 260 °C or below (molten solder temperature)

• Time 10 seconds or less

• Number of times One

• Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of

0.2 Wt % is recommended.)

(3) Cautions

Fluxes

Avoid removing the residual flux with freon-based and chlorine-based cleaning solvent.

[MEMO]

CAUTION

Within this device there exists GaAs (Gallium Arsenide) material which is a harmful substance if ingested. Please do not under any circumstances break the hermetic seal.

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 - "Standard", "Special", and "Specific". The Specific quality grade applies only to devices developed based on a customer designated "quality assurance program" for a specific application. The recommended applications of a device depend on its quality grade, as indicated below. Customers must check the quality grade of each device before using it in a particular application.
 - Standard: Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots
 - Special: Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)
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